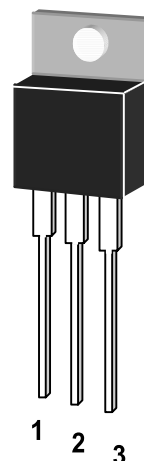


ST H1061

NPN Plastic Power Transistor
Low frequency power amplifier



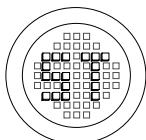
1. Base 2. Collector 3. Emitter

TO-220 Plastic Package

Absolute Maximum Ratings ($T_a = 25^{\circ}\text{C}$)

	Symbol	Value	Unit
Collector Emitter Voltage	V_{CEO}	50	V
Collector Base Voltage	V_{CBO}	50	V
Emitter Base Voltage	V_{EBO}	4	V
Collector Current	I_C	3	A
Power Dissipation	P_{tot}	25	W
Junction Temperature	T_j	150	$^{\circ}\text{C}$
Storage Temperature Range	T_S	-45 to +150	$^{\circ}\text{C}$

G S P FORM A IS AVAILABLE



®

РАДИОТЕХ

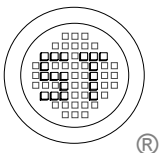
Тел.: (495) 795-0805
Факс: (495) 234-1603
Эл. почта: info@rct.ru
Веб: www.rct.ru

ST H1061

Characteristics at $T_{amb}=25\text{ }^{\circ}\text{C}$

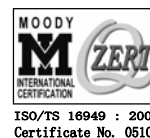
	Symbol	Min.	Typ.	Max.	Unit	
DC Current Gain at $V_{CE}=4\text{V}$, $I_C=1\text{A}$	H1061A	h_{FE}	35	-	70	-
	H1061B	h_{FE}	60	-	120	-
	H1061C	h_{FE}	100	-	200	-
	H1061D	h_{FE}	160	-	320	-
	at $V_{CE}=4\text{V}$, $I_C=0.1\text{A}$	h_{FE}	35	-	-	-
Collector Cutoff Current at $V_{CB}=20\text{V}$	I_{CBO}	-	-	0.1	mA	
Collector Saturation Voltage at $I_C=2\text{A}$, $I_B=0.2\text{A}$	$V_{CE(sat)}$	-	-	1	V	
Collector Emitter Breakdown Voltage at $I_C=50\text{mA}$	$V_{(BR)CEO}$	50	-	-	V	
Collector Base Breakdown Voltage at $I_C=5\text{mA}$	$V_{(BR)CBO}$	50	-	-	V	
Emitter Base Breakdown Voltage at $I_E=5\text{mA}$	$V_{(BR)EBO}$	4	-	-	V	
Base Emitter Voltage at $I_C=1\text{A}$, $V_{CE}=4\text{V}$	V_{BE}	-	-	1.5	V	
Gain Bandwidth Product at $V_{CE}=4\text{V}$, $I_C=0.5\text{A}$	f_T	-	8	-	MHz	

G S P FORM A IS AVAILABLE



SEMTECH ELECTRONICS LTD.

(Subsidiary of Semtech International Holdings Limited, a company listed on the Hong Kong Stock Exchange, Stock Code: 724)



Dated : 07/12/2002